L Number	Hits	Search Text	DB	Time stamp
1	77763	414/\$.ccls.	USPAT;	2003/11/25 12:27
) )			US-PGPUB;	
1			EPO; JPO;	
i			DERWENT;	
	440	444/0	IBM_TDB	
2	416	414/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT;	2003/11/25 13:08
		near3 (bond\$4 or stack\$4))	US-PGPUB;	
1			EPO; JPO;	
ļ			DERWENT;	
3	291	414/\$.ccls. and ((die or chip or semiconductor) near3	USPAT;	2003/11/25 12:30
		(bond\$4 or stack\$4))	US-PGPUB:	2003/11/23 12:00
i l			EPO; JPO;	
			DERWENT	
}			IBM_TDB	
4	11	(414/\$.ccls. and ((die or chip or semiconductor) near3	USPAT;	2003/11/25 12:31
		(bond\$4 or stack\$4))) and (introduc\$4 near3 wafer)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
5	80782	((die or chip or semiconductor) near3 (bond\$4 or stack\$4))	USPAT;	2003/11/25 12:30
			US-PGPUB;	
]			EPO; JPO;	
,	i		DERWENT;	
6	278	(((die or chip or semiconductor) near3 (bond\$4 or stack\$4)))	IBM_TDB   USPAT;	2003/11/25 12:31
	210	and (introduc\$4 near3 wafer)	US-PGPUB;	2003/11/25 12.51
!		and (introducted fieuro water)	EPO; JPO;	,
			DERWENT:	
			IBM_TDB	
7	0	((((die or chip or semiconductor) near3 (bond\$4 or stack\$4)))	USPAT;	2003/11/25 12:31
		and (introduc\$4 near3 wafer)) and ((introduc\$4 near3 wafer)	US-PGPUB;	
)		with (stacker or bonder))	EPO; JPO;	
[			DERWENT;	
			IBM_TDB	
8	0	((introduc\$4 near3 wafer) with (stacker or bonder))	USPAT;	2003/11/25 12:32
, ,			US-PGPUB;	ļ
			EPO; JPO;	
			DERWENT; IBM_TDB	
9	325	(wafer with (stacker or bonder))	USPAT;	2003/11/25 12:32
-	525	( ( danier of bolistif)	US-PGPUB:	
1			EPO; JPO;	
	Į.		DERWENT;	
			IBM_TDB	
10	252	((wafer with (stacker or bonder))) and ((die or chip or	USPAT;	2003/11/25 13:08
ļ (	Į	substrate or semiconductor) near3 (bond\$4 or stack\$4))	US-PGPUB;	
			EPO; JPO;	
1	İ		DERWENT;	
11	672	438/455.ccls.	IBM_TDB   USPAT;	2003/11/25 13:08
'	0/2	430/400.00IS.	US-PGPUB;	2003/11/25 13.08
	ľ		EPO; JPO;	1
ł	l		DERWENT:	l
			IBM_TDB	
12	484	438/455.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 13:52
		semiconductor) near3 (bond\$4 or stack\$4))	US-PGPUB;	
1	Ì	,	EPO; JPO;	
	ļ		DERWENT;	
			IBM_TDB	

	-T			
13	117	438/455.ccls. and ((die or chip or substrate or semiconductor) near3 (stack\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/25 13:43
14	O	(((carrying or carried or convey\$4 or transfer\$4 or introduc\$4 or transport\$4) near4 wafer) with ((into or inside or in) near3 (bonder or stacker)))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/25 13:48
15	38706	((carrying or carried or convey\$4 or transfer\$4 or introduc\$4 or transport\$4) near4 wafer)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/25 13:47
16	42831	((carrying or carried or convey\$4 or transfer\$4 or introduc\$4 or transport\$4) near4 wafer)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/25 13:47
17	16	(((carrying or carried or convey\$4 or transfer\$4 or introduc\$4 or transport\$4) near4 wafer) ) and ((into or inside or in) near3 (bonder or stacker))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/25 13:51
18	491	438/109.ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/25 13:51
19	288	438/109.ccls. and ((die or chip or substrate or semiconductor) near3 stack\$4)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/25 13:52
20	16	(438/109.ccls. and ((die or chip or substrate or semiconductor) near3 stack\$4)) and (bonder or stacker)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/25 13:52
21	8	(US-6560857-\$ or US-5979739-\$ or US-6566232-\$ or US-6177296-\$).did. or (US-20030145939-\$ or US-20020092622-\$ or US-20010013643-\$ or	DERWENT; IBM_TDB USPAT; US-PGPUB	2003/11/25 13:56
22	14	US-20020092022-\$ 01 US-20010013043-\$ 01 US-20030106209-\$).did.  (US-6514795-\$ or US-6337227-\$ or US-6620651-\$ or US-6506664-\$ or US-6376265-\$ or US-6165815-\$ or US-5952725-\$ or US-3591921-\$ or US-6617198-\$ or US-5804004-\$ or US-6428641-\$).did. or (US-20020004288-\$	USPAT; US-PGPUB	2003/11/25 13:56
23	6	or US-20030060034-\$ or US-20020185704-\$).did.	USPAT; US-PGPUB	2003/11/25 14:24
-	143799	438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/10/18 14:21
-	3103	438/\$.ccls. and (die near4 bond\$4)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/18 14:27

	.,			
-	346	(438/\$.ccls. and (die near4 bond\$4)) and (stack\$4 near4 (chip or die or device or semiconductor))	USPAT; US-PGPUB;	2003/10/18 14:27
			EPO; JPO; DERWENT;	
		(/439/C and a good (dia nagget based 04)) and (at a short of a saget	IBM_TDB	00004040404407
-	8	((438/\$.ccls. and (die near4 bond\$4)) and (stack\$4 near4 (chip or die or device or semiconductor))) and (die near3	USPAT; US-PGPUB;	2003/10/18 14:27
		bonder)	EPO; JPO;	
			DERWENT;	
_	104030	156/\$.ccls.	IBM_TDB USPAT:	2003/10/18 14:27
	104000	100/\$.0013.	US-PGPUB;	2003/10/16 14.2/
			EPO; JPO;	
			DERWENT;	
_	733	156/\$.ccls. and (die near4 bond\$4)	IBM_TDB   USPAT;	2003/10/18 14:27
		10074.00.0. dira (die riedi i beriati i)	US-PGPUB;	2000/10/10 14:2/
	]		EPO; JPO;	
			DERWENT;	
_	29	(156/\$.ccls. and (die near4 bond\$4)) and (stack\$4 near4	IBM_TDB   USPAT;	2003/10/18 14:31
		(chip or die or device or semiconductor))	US-PGPUB,	
			EPO; JPO;	
			DERWENT; IBM TDB	
-	4231	438/106,109,113,114,118,119.ccls.	USPAT;	2003/10/18 15:19
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	17583	(carrying or introducing) same wafer	USPAT;	2003/10/18 14:34
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	132	438/106,109,113,114,118,119.ccls. and ((carrying or	USPAT;	2003/10/18 14:35
		introducing) same wafer)	US-PGPUB; EPO; JPO;	
			DERWENT;	
	1.4	(400/400 400 440 444 440 440 ask and (/asymptomage	IBM_TDB	00004040404440
-	14	(438/106,109,113,114,118,119.ccls. and ((carrying or introducing) same wafer)) and (((carrying or introducing)	USPAT; US-PGPUB;	2003/10/18 14:42
		same wafer) same (die near4 bond\$4))	EPO; JPO;	
			DERWENT;	
_	77	(((carrying or introducing) same wafer) same (die near4	IBM_TDB   USPAT;	2003/10/18 14:42
	''	(((Carrying of introducing) same water) same (die hear4   bond\$4))	US-PGPUB;	2000/10/10 14.42
			EPO; JPO;	
[			DERWENT; IBM_TDB	
_	63	( (((carrying or introducing) same wafer) same (die near4	USPAT;	2003/10/18 14:42
		bond\$4))) not ((438/106,109,113,114,118,119.ccls. and	US-PGPUB;	
		((carrying or introducing) same wafer)) and (((carrying or introducing) same wafer) same (die near4 bond\$4)))	EPO; JPO;	
		introducing) same water) same (die near4 pond\$4)))	DERWENT; IBM_TDB	
-	15	(( (((carrying or introducing) same wafer) same (die near4	USPAT;	2003/10/18 14:59
		bond\$4))) not ((438/106,109,113,114,118,119.ccls. and	US-PGPUB;	
		((carrying or introducing) same wafer)) and (((carrying or introducing) same wafer) same (die near4 bond\$4)))) and	EPO; JPO; DERWENT;	
		stack\$4	IBM_TDB	
-	2	("6602773").PN.	USPAT;	2003/10/18 15:18
	1		US-PGPUB; EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	

	1	("E962925"   "6004660"   "6044244"   "6066550") DN	USPAT	0000/40/40 45:00
-	481	("5863835"   "6001660"   "6011311"   "6066559").PN.		2003/10/18 15:00
-	401	438/109.ccls.	USPAT;	2003/10/18 15:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
ļ .			IBM_TDB	
-	4	438/109.ccls. and ((die or chip or device or semiconductor)	USPAT;	2003/10/18 15:20
l i		near4 (bonder))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	145296	438/\$.ccls.	USPAT;	2003/11/25 10:22
}			US-PGPUB;	
			EPO, JPO;	
			DERWENT;	
			IBM_TDB	
-	241	438/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT:	2003/11/25 12:01
ĺ		near3 bonder)	US-PGPUB;	2000/11/20 12:01
		, incare benedity	EPO; JPO;	
	1		DERWENT;	
_	23	(438/\$.ccls. and ((die or chip or substrate or semiconductor)	IBM_TDB	2003/11/25 10:37
-	23		USPAT;	2003/11/25 10.37
<u> </u>		near3 bonder)) and ((die or chip or substrate or	US-PGPUB;	
	,	semiconductor) near3 stack\$4)	EPO; JPO;	
i			DERWENT;	
1			IBM_TDB	
-	422	438/458,ccls.	USPAT;	2003/11/25 10:35
,			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	59	438/458.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 12:01
		semiconductor) near3 stack\$4)	US-PGPUB;	
			EPO; JPO;	•
			DERWENT;	
			IBM_TDB	
! _	2	(438/458.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 11:44
		semiconductor) near3 stack\$4)) and ((die or chip or substrate	US-PGPUB;	
! !		or semiconductor) near3 bonder)	EPO; JPO;	
i		,	DERWENT:	
[			IBM TDB	
-	57	(438/458.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 11:43
		semiconductor) near3 stack\$4)) not ((438/458.ccls. and ((die	US-PGPUB:	
)	'	or chip or substrate or semiconductor) near3 stack\$4)) and	EPO: JPO:	
		((die or chip or substrate or semiconductor) near3 bonder))	DERWENT;	
		1/ 2. 2. 2   1. 2	IBM_TDB	
_	1218	438/118,119.ccls.	USPAT;	2003/11/25 11:44
(	1210		US-PGPUB;	
j į	İ		EPO; JPO;	
<u> </u>			DERWENT;	
			IBM_TDB	
_	36	138/118 110 ccls, and (/die or chin or substrate or	USPAT;	2003/11/25 11:48
-	30	438/118,119.ccls. and ((die or chip or substrate or		2003/11/23 11.40
	i	semiconductor) near3 bonder)	US-PGPUB;	1
			EPO; JPO;	
			DERWENT;	
ļ	24	(	IBM_TDB	0000/44/05 44:40
-	21	(438/118,119.ccls. and ((die or chip or substrate or	USPAT;	2003/11/25 11:48
		semiconductor) near3 bonder)) and wafer	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	L

-	672	438/455.ccls.	USPAT;	2003/11/25 11:48
1	1		US-PGPUB;	
1			EPO: JPO:	
Į.			DERWENT:	
1	1		IBM TDB	
-	8	438/455.ccls. and ((die or chip or substrate or	USPAT:	2003/11/25 11:51
İ		semiconductor) near3 bonder)	US-PGPUB:	
		,,	EPO; JPO;	
1	}		DERWENT:	
			IBM TDB	
_	2479	438/460-465.ccls.	USPAT:	2003/11/25 11:51
		100/100 100.0010.	US-PGPUB:	2000/11/20 11.01
			EPO; JPO;	
			DERWENT	
1				
_	21	438/460 465 cels, and (/dip or chip or substrate or	IBM_TDB	2002/11/25 12:29
1	4	438/460-465.ccls. and ((die or chip or substrate or semiconductor) near3 bonder)	USPAT;	2003/11/25 12:28
		Sermiconductory nears bondery	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0.455	400/400 405   1   1 /400/400 405   1   1 /400/400	IBM_TDB	000011110511
[ -	2458	438/460-465.ccls. not (438/460-465.ccls. and ((die or chip or	USPAT;	2003/11/25 11:55
1		substrate or semiconductor) near3 bonder))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	90	(438/460-465.ccls. not (438/460-465.ccls. and ((die or chip or	USPAT;	2003/11/25 12:01
		substrate or semiconductor) near3 bonder))) and ((die or chip	US-PGPUB;	
		or substrate or semiconductor) near3 stack\$4)	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	104462	156/\$.ccls.	USPAT;	2003/11/25 12:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT,	
			IBM TDB	
_	75	156/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT;	2003/11/25 12:01
		near3 bonder)	US-PGPUB:	
		,	EPO; JPO;	
	(		DERWENT;	
			IBM_TDB	
1 -	3	(156/\$.ccls. and ((die or chip or substrate or semiconductor)	USPAT;	2003/11/25 12:05
1		near3 bonder)) and ((die or chip or substrate or	US-PGPUB	2000/11/20 12:00
		semiconductor) near3 stack\$4)	EPO; JPO;	
1	1	John John Grand Stacky	DERWENT;	
1	1		IBM TDB	
1	79	((438/460-465.ccls. not (438/460-465.ccls. and ((die or chip	USPAT:	2003/11/25 12:06
1	/9		· '	2003/11/23 12.00
	Į l	or substrate or semiconductor) near3 bonder))) and ((die or chip or substrate or semiconductor) near3 stack\$4)) and	US-PGPUB;	
		cnip or substrate or semiconductor) near3 stack\$4)) and   wafer	EPO; JPO;	
1		Walei	DERWENT;	
			IBM_TDB	L